



PATENT
Dkt. 2271/62289-Z

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Seiji SARAYAMA et al.

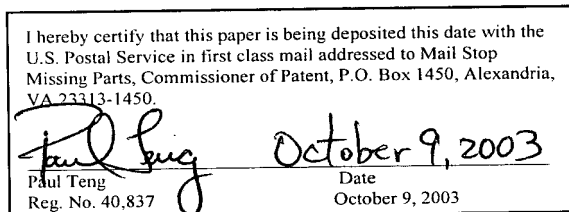
Serial No. : 10/601,301

Group Art Unit: 1765

Date Filed : June 13, 2003

Examiner:

For : PRODUCTION OF A GaN BULK CRYSTAL SUBSTRATE AND
A SEMICONDUCTOR DEVICE FORMED ON A GaN BULK
CRYSTAL SUBSTRATE



1185 Avenue of the Americas
New York, New York 10036
(212) 278-0400
October 9, 2003

**RESPONSE TO "NOTICE TO FILE CORRECTED APPLICATION PAPERS" AND
REQUEST FOR CORRECTED FILING RECEIPT**

Mail Stop Missing Parts
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 23313-1450

Sir:

In response to the Notice to File Corrected Application Papers-Filing Date Granted dated September 15, 2003, applicants hereby submit (1) copy of the Notice, and (2) two sets of formal drawings, Figs. 1-21.

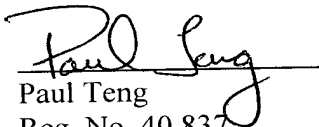
Applicants also enclose a copy of the official filing receipt, which erroneously states the title as: -Production of a GaN bulk crystal substrate and a semiconductor device formed on a GuN bulk crystal substrate-, rather than -Production of a GaN bulk crystal substrate and

a semiconductor device formed on a ~~GaN~~ GaN bulk crystal substrate--.

Applicants hereby respectfully request that a corrected filing receipt be issued showing the correct title.

No fee is believed to be due. However, please charge any additional fees or credit any overpayment to our deposit account number 03-3125. A copy of this sheet is enclosed.

Respectfully submitted,


Paul Teng
Reg. No. 40,837

Encls.